



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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SxX8xSx Series



**Main Features**

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
$V_{DRM}/V_{RRM}$	400 to 800	V
$I_{GT}$	5 to 200	$\mu A$

**Applications**

The SxX8xSx EV series is specifically designed for GFCI (Ground Fault Circuit Interrupter) and gas ignition applications.

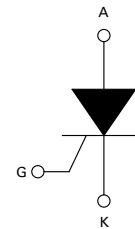
**Description**

New device series offers high static dv/dt and lower turn off ( $t_q$ ) sensitive SCR with its small die planar construction design. It is specifically designed for GFCI (Ground Fault Circuit Interrupter) and Gas Ignition applications. All SCRs junctions are glass-passivated to ensure long term reliability and parametric stability.

**Features**

- RoHS compliant and Halogen-Free
- Thru-hole and surface mount packages
- Surge current capability > 10Amps
- Blocking voltage ( $V_{DRM}/V_{RRM}$ ) capability - up to 800V
- High dv/dt noise immunity
- Improved turn-off time ( $t_q$ ) < 25  $\mu$ sec
- Sensitive gate for direct microprocessor interface

**Schematic Symbol**



**Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-92 $T_c = 55^\circ C$	0.8 A
		SOT-89 $T_c = 60^\circ C$	0.8 A
		SOT-223 $T_L = 60^\circ C$	0.8 A
$I_{T(AV)}$	Average on-state current	TO-92 $T_c = 55^\circ C$	0.51 A
		SOT-89 $T_c = 60^\circ C$	0.51 A
		SOT-223 $T_L = 60^\circ C$	0.51 A
$I_{TSM}$	Non repetitive surge peak on-state current (Single cycle, $T_j$ initial = 25°C)	TO-92 $F = 50Hz$	8 A
		SOT-89 $F = 60Hz$	10 A
$I^2t$	$I^2t$ Value for fusing	$t_p = 10$ ms $F = 50$ Hz	0.32 $A^2s$
		$t_p = 8.3$ ms $F = 60$ Hz	0.41 $A^2s$
di/dt	Critical rate of rise of on-state current $I_G = 10mA$	TO-92 $T_j = 125^\circ C$ SOT-89 SOT-223	50 $A/\mu s$
$I_{GM}$	Peak Gate Current	$t_p = 10$ $\mu s$ $T_j = 125^\circ C$	1.0 A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ C$	0.1 W
$T_{stg}$	Storage junction temperature range	—	-40 to 150 $^\circ C$
$T_J$	Operating junction temperature range	—	-40 to 125 $^\circ C$

**Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified)**

Symbol	Description	Test Conditions	Limit	Value			Unit
				SxX8yS1	SxX8yS2	SxX8yS	
I <sub>GT</sub>	DC Gate Trigger Current	V <sub>D</sub> = 6V R <sub>L</sub> = 100 Ω	MIN.	0.5	1	15	μA
			MAX.	5	50	200	μA
V <sub>GT</sub>	DC Gate Trigger Voltage	V <sub>D</sub> = 6V R <sub>L</sub> = 100 Ω	MAX.	0.8			V
V <sub>G<sub>RM</sub></sub>	Peak Reverse Gate Voltage	I <sub>RG</sub> = 10μA	MIN.	5			V
I <sub>H</sub>	Holding Current	R <sub>GK</sub> = 1 kΩ Initial Current = 20mA	MAX.	5			mA
(dv/dt) <sub>s</sub>	Critical Rate-of-Rise of Off-State Voltage	T <sub>J</sub> = 125°C V <sub>D</sub> = V <sub>DRM</sub> / N <sub>RRM</sub> Exp. Waveform R <sub>GK</sub> = 1 kΩ	MIN.	75			V/μs
V <sub>GD</sub>	Gate Non-Trigger Voltage	V <sub>D</sub> = V <sub>DRM</sub> R <sub>GK</sub> = 1 kΩ T <sub>J</sub> = 25°C	MIN.	0.2			V
t <sub>q</sub>	Turn-Off Time	T <sub>J</sub> = 25°C @ 600 V R <sub>GK</sub> = 1 kΩ	MAX.	30	25	25	μs
t <sub>gt</sub>	Turn-On Time	I <sub>G</sub> = 10mA PW = 15μsec I <sub>T</sub> = 1.6A(pk)	TYP.	2.0	2.0	2.0	μs

Note: x = voltage, y = package

**Static Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified)**

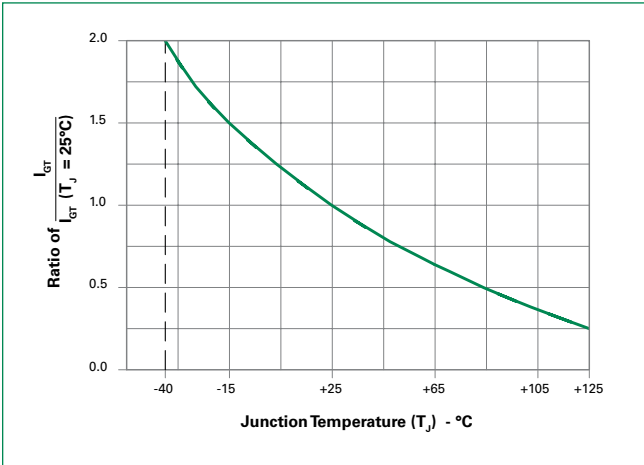
Symbol	Description	Test Conditions	Limit	Value	Unit
V <sub>TM</sub>	Peak On-State Voltage	I <sub>TM</sub> = 1.6A (pk)	MAX.	1.70	V
I <sub>DRM</sub>	Off-State Current, Peak Repetitive	T <sub>J</sub> = 25°C @ V <sub>D</sub> = V <sub>DRM</sub> R <sub>GK</sub> = 1 kΩ	MAX.	3	μA
		T <sub>J</sub> = 125°C @ V <sub>D</sub> = V <sub>DRM</sub> R <sub>GK</sub> = 1 kΩ	MAX.	500	μA

**Thermal Resistances**

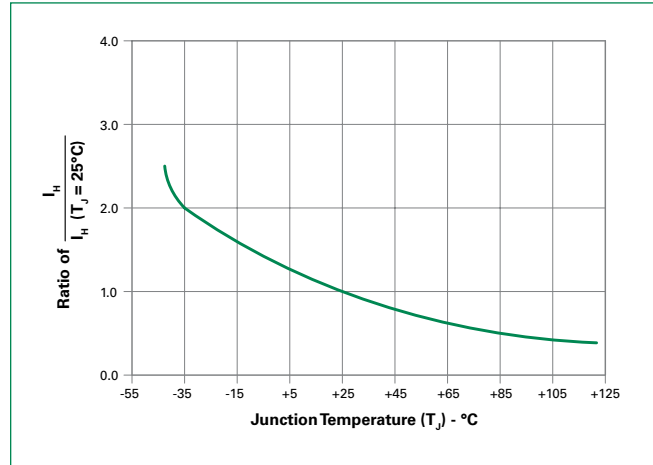
Symbol	Description	Test Conditions	Value	Unit	
R <sub>th(j-c)</sub>	Junction to case (AC)	I <sub>T</sub> = 0.8A <sub>(RMS)</sub> <sup>1</sup>	TO-92	75	°C/W
			SOT-223	30	°C/W
			SOT-89	50	°C/W
R <sub>th(j-a)</sub>	Junction to ambient	I <sub>T</sub> = 0.8A <sub>(RMS)</sub> <sup>1</sup>	TO-92	150	°C/W
			SOT-223	60	°C/W
			SOT-89	90	°C/W

<sup>1</sup> 60Hz AC resistive load condition, 100% conduction.

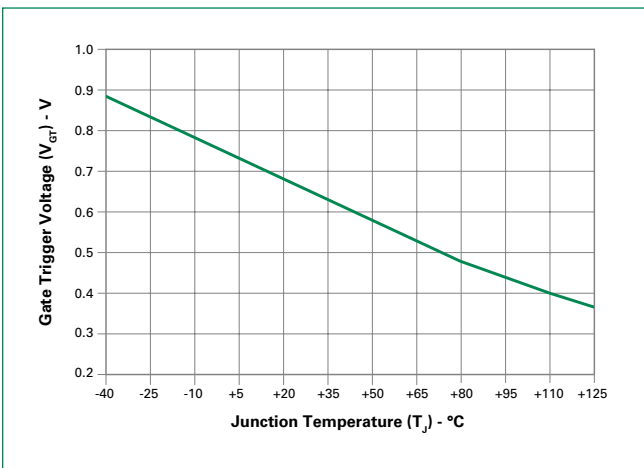
**Figure 1: Normalized DC Gate Trigger Current For All Quadrants vs. Junction Temperature**



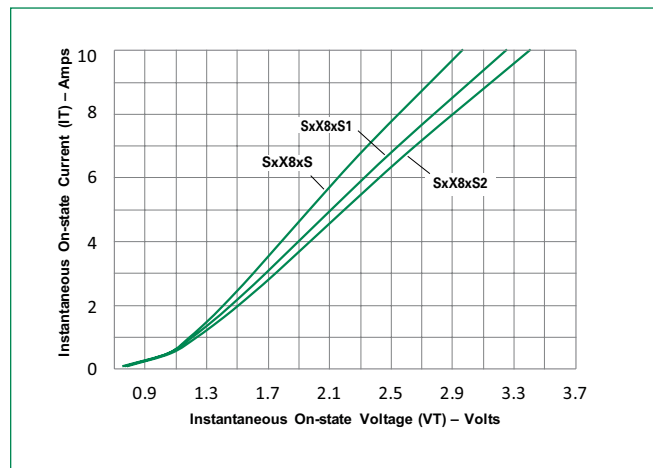
**Figure 2: Normalized DC Holding Current vs. Junction Temperature**



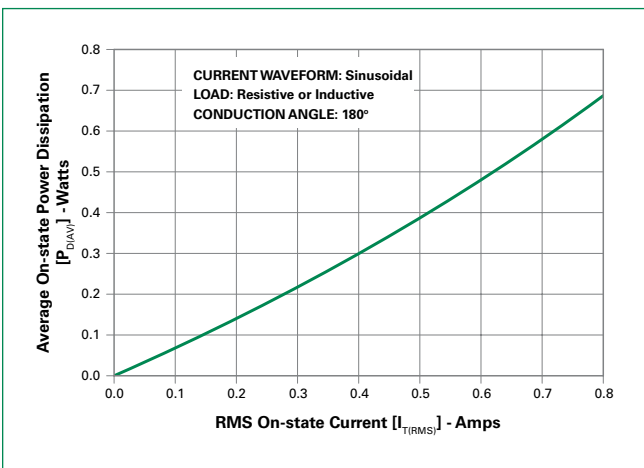
**Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature**



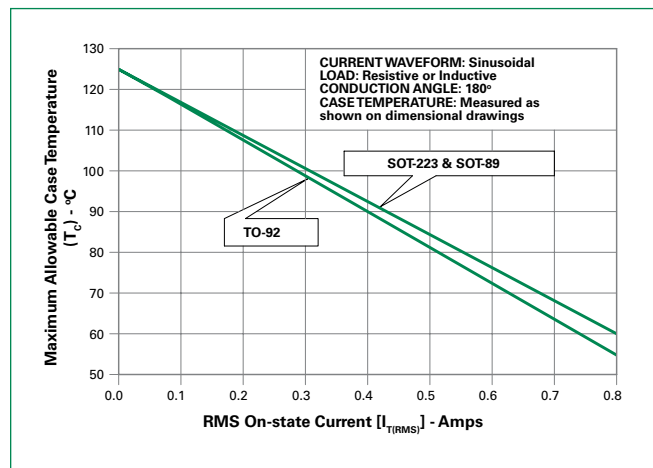
**Figure 4: On-State Current vs. On-State Voltage (Typical)**



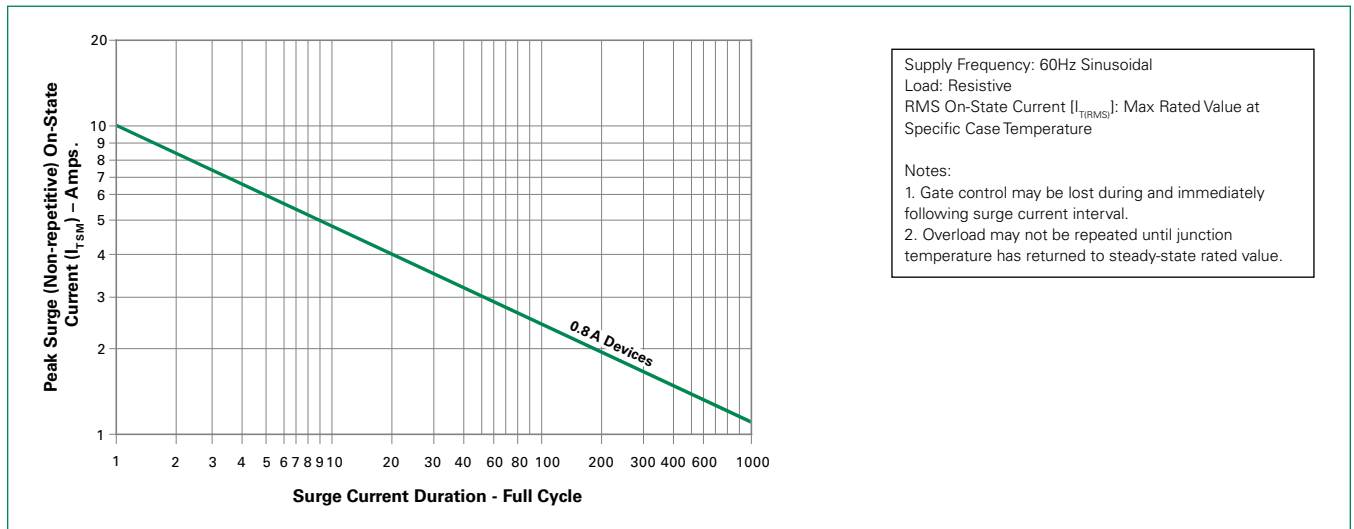
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



**Figure 6: Maximum Allowable Case Temperature vs. On-State Current**

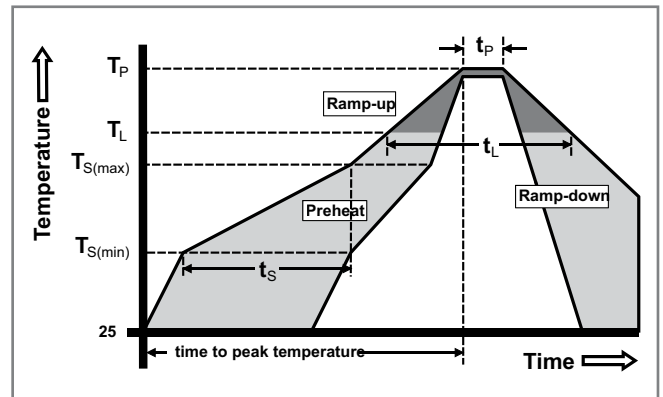


**Figure 7: Surge Peak On-State Current vs. Number of Cycles**



**Soldering Parameters**

Reflow Condition	Pb – Free assembly	
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Time (min to max) ( $t_s$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



**Additional Information**



Datasheet



Resources



Samples

**Physical Specifications**

<b>Terminal Finish</b>	100% Matte Tin-plated.
<b>Body Material</b>	UL recognized epoxy meeting flammability classification 94V-0.
<b>Lead Material</b>	Copper Alloy

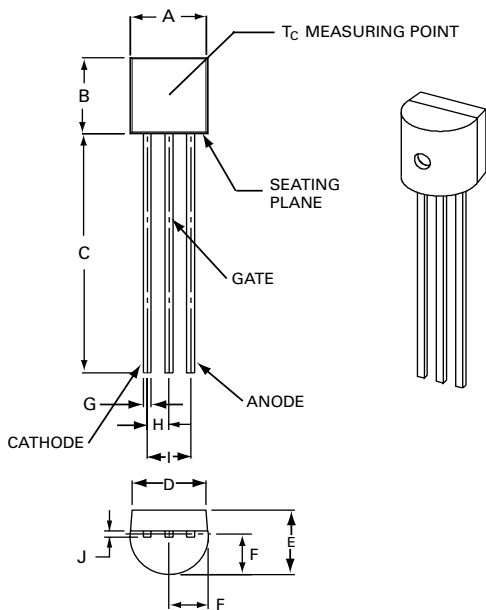
**Design Considerations**

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

**Reliability/Environmental Tests**

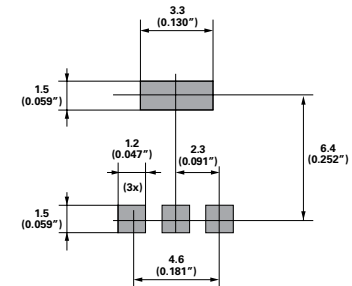
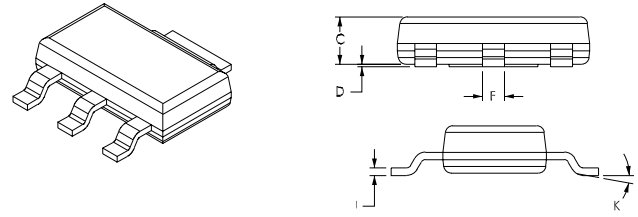
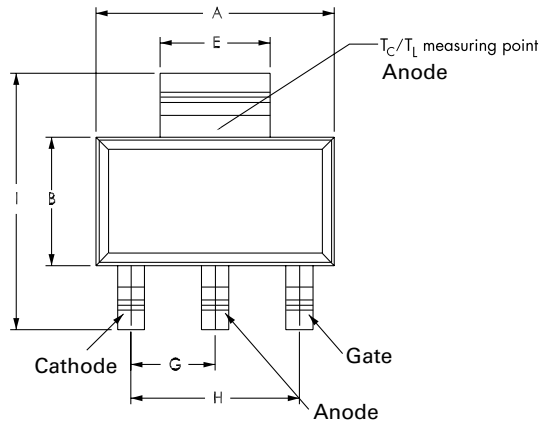
Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 110°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

**Dimensions – TO-92**



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.175	0.205	4.450	5.200
B	0.170	0.210	4.320	5.330
C	0.500		12.70	
D	0.135		3.430	
E	0.125	0.165	3.180	4.190
F	0.080	0.105	2.040	2.660
G	0.016	0.021	0.407	0.533
H	0.045	0.055	1.150	1.390
I	0.095	0.105	2.420	2.660
J	0.015	0.020	0.380	0.500

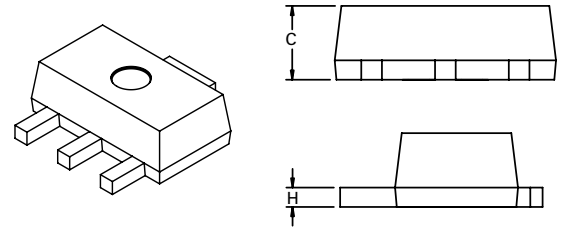
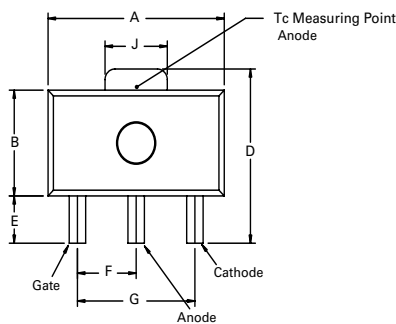
**Dimensions – SOT-223**



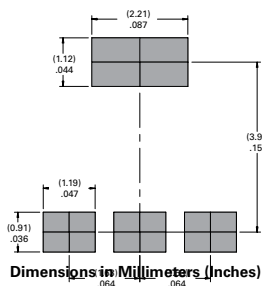
Dimensions in Millimeters (Inches)

Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.248	0.256	0.264	6.30	6.50	6.70
B	0.130	0.138	0.146	3.30	3.50	3.70
C	—	—	0.071	—	—	1.80
D	0.001	—	0.004	0.02	—	0.10
E	0.114	0.118	0.124	2.90	3.00	3.15
F	0.024	0.027	0.034	0.60	0.70	0.85
G	—	0.090	—	—	2.30	—
H	—	0.181	—	—	4.60	—
I	0.264	0.276	0.287	6.70	7.00	7.30
J	0.009	0.010	0.014	0.24	0.26	0.35
K	10° MAX					

**Dimensions – SOT-89**



**Pad Layout for SOT-89**



Dimensions in Millimeters (Inches)

Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.173	—	0.181	4.40	—	4.60
B	0.090	—	0.102	2.29	—	2.60
C	0.055	—	0.063	1.40	—	1.60
D	0.155	—	0.167	3.94	—	4.25
E	0.035	—	0.047	0.89	—	1.20
F	0.056	—	0.062	1.42	—	1.57
G	0.115	—	0.121	2.92	—	3.07
H	0.014	—	0.017	0.35	—	0.44
I	0.014	—	0.019	0.36	—	0.48
J	0.064	—	0.072	1.62	—	1.83

**Product Selector**

Part Number	Voltage			Gate Sensitivity	Package
	400V	600V	800V		
S4X8ES	X	—	—	200 $\mu$ A	TO-92
S6X8ES	—	X	—	200 $\mu$ A	TO-92
S8X8ES	—	—	X	200 $\mu$ A	TO-92
S4X8TS	X	—	—	200 $\mu$ A	SOT-223
S6X8TS	—	X	—	200 $\mu$ A	SOT-223
S8X8TS	—	—	X	200 $\mu$ A	SOT-223
S4X8BS	X	—	—	200 $\mu$ A	SOT-89
S6X8BS	—	X	—	200 $\mu$ A	SOT-89
S4X8ES1	X	—	—	5 $\mu$ A	TO-92
S6X8ES1	—	X	—	5 $\mu$ A	TO-92
S8X8ES1	—	—	X	5 $\mu$ A	TO-92
S4X8TS1	X	—	—	5 $\mu$ A	SOT-223
S6X8TS1	—	X	—	5 $\mu$ A	SOT-223
S8X8TS1	—	—	X	5 $\mu$ A	SOT-223
S4X8ES2	X	—	—	50 $\mu$ A	TO-92
S6X8ES2	—	X	—	50 $\mu$ A	TO-92
S8X8ES2	—	—	X	50 $\mu$ A	TO-92
S4X8TS2	X	—	—	50 $\mu$ A	SOT-223
S6X8TS2	—	X	—	50 $\mu$ A	SOT-223
S8X8TS2	—	—	X	50 $\mu$ A	SOT-223

**Packing Options**

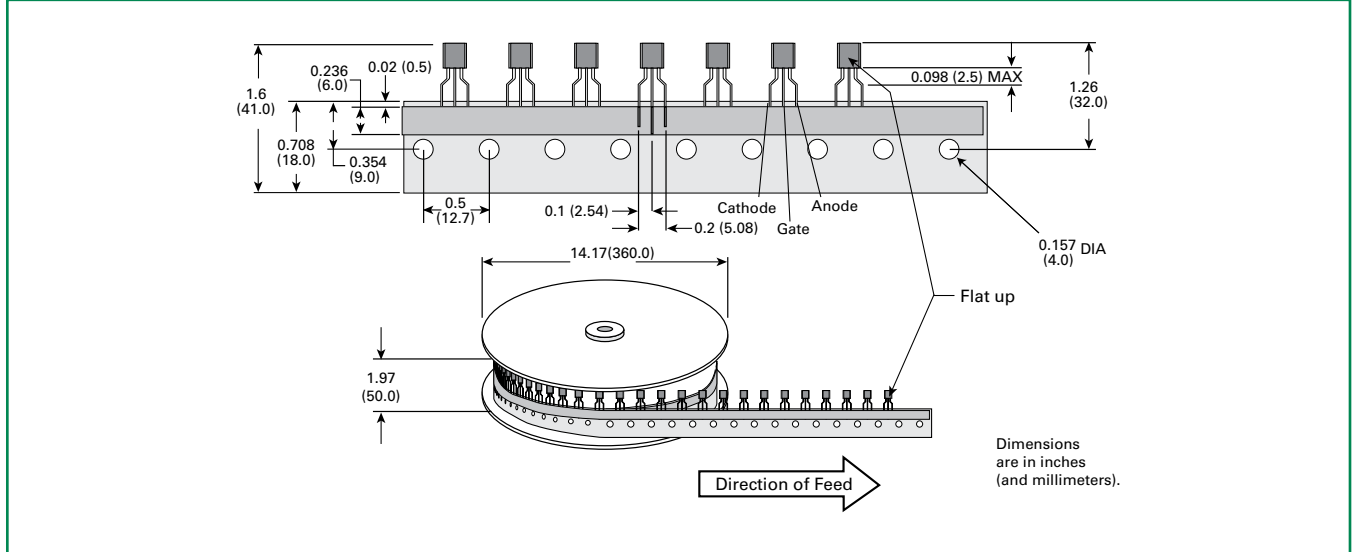
Part Number	Marking	Weight	Packing Mode	Base Quantity
SxX8ESy	SxX8ESy	0.217g	Bulk	2500
SxX8ESyAP	SxX8ESy	0.217g	Ammo Pack	2000
SxX8ESyRP	SxX8ESy	0.217g	Tape & Reel	2000
SxX8TSyRP	SxX8TSy	0.120g	Tape & Reel	1000
SxX8BSRP	xX8	0.053g	Tape & Reel	1000
SxX8BSRP1	xX8	0.053g	Tape & Reel	1000

Note: x = voltage, y = gate sensitivity



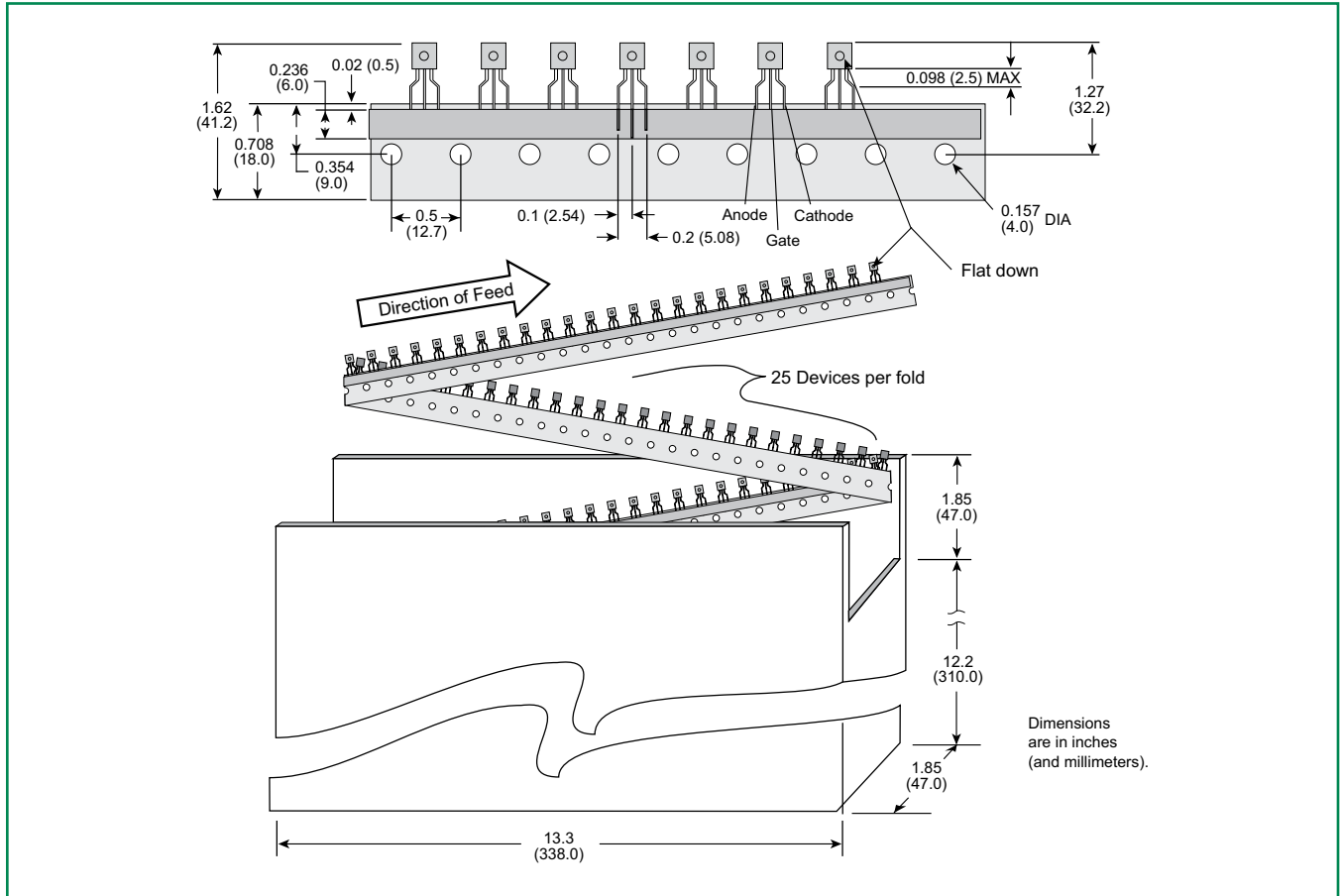
**TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications**

Meets all EIA-468-C Standards

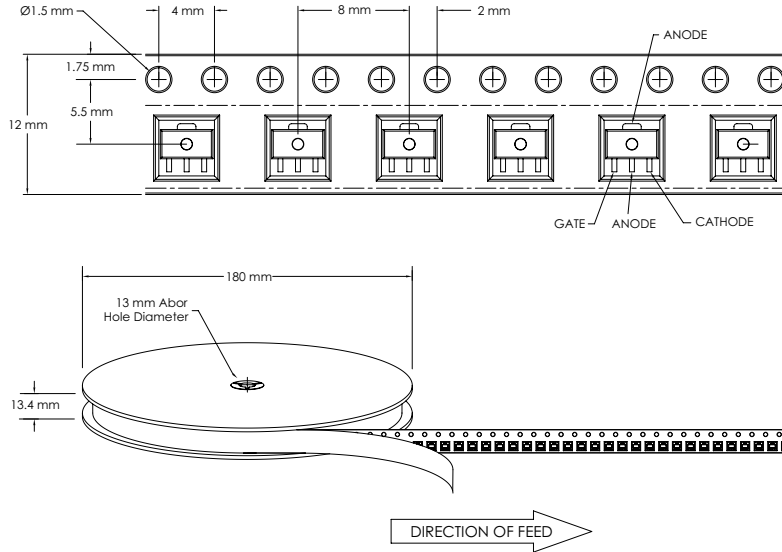


**TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications**

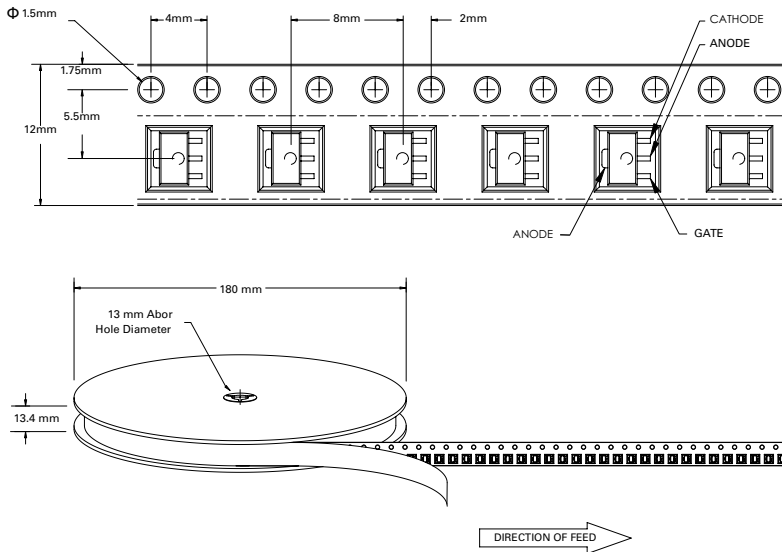
Meets all EIA-468-C Standards



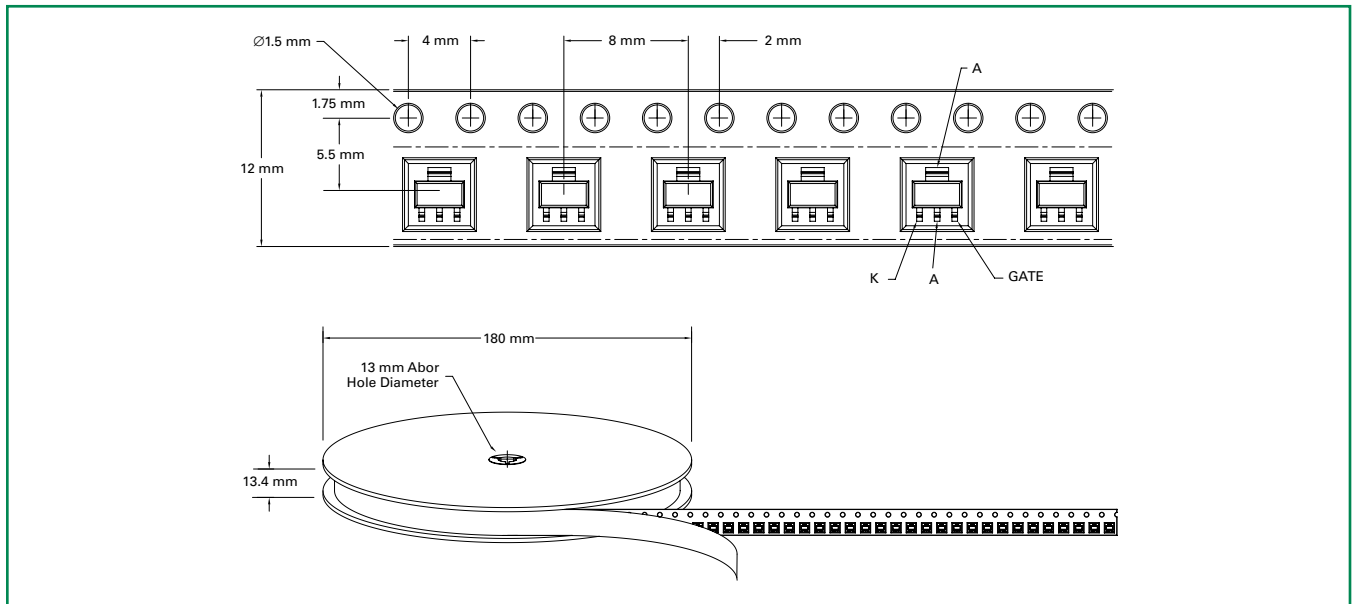
**SOT-89 Reel Pack (RP) Specifications**



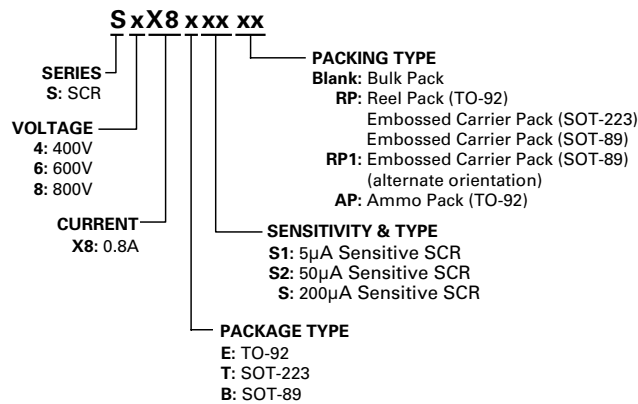
**SOT-89 Reel Pack (RP1) Specifications**



**SOT-223 Reel Pack (RP) Specifications**



**Part Numbering System**



**Part Marking System**

